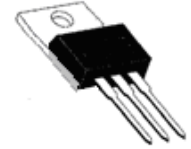




# IRFV260



## Power MOSFET(N-channel) Transistor

### Features:

1. It's voltage control component with good input impedance, small starting power dissipation, wide area of safe operation, good temperature stability.
2. Implementation of standards: QZJ840611
3. Use for high speed switch, circuit of power source contravariance.
4. Quality Class: GS, G.

### TECHNICAL DATA:

(Ta = 25°C )

Parameter name	Symbols	Unit	Specifications	Test Condition
Drain-Source Voltage	V <sub>DSS</sub>	V	200(max.)	
Drain Current	I <sub>D</sub>	A	45(max.)	
Total Power Dissipation	P <sub>D</sub>	W	300(max.)	(Tc=25°C)
Gate-Source Voltage	V <sub>GSS</sub>	V	±20(max.)	
Junction Temperature	T <sub>jm</sub>	°C	150	
Storage Temperature	T <sub>stg</sub>	°C	-55~+150	
Drain-Source Breakdown Voltage	V <sub>(BR)OSS</sub>	V	Min.:200	V <sub>GS</sub> =0V, I <sub>D</sub> =1mA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	Ohms	Max.:0.06	V <sub>GS</sub> =10V, I <sub>D</sub> =22.5A
Gate Threshold Voltage	V <sub>GS(th)</sub>	V	Min.:2, Max.:4	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	uA	Max.:1000	V <sub>GS</sub> =0V, V <sub>DS</sub> =160V
Gate-Body Leakage	I <sub>GSS</sub>	nA	Max.:100	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V

### Outline and Dimensions: